

ABSTRACT OF THE DISCLOSURESiCOI TYPE COMPOSITE SUBSTRATE MANUFACTURING METHOD COMPRISING  
AN EPITAXY STEP

The invention relates to an SiCOI type composite substrate manufacturing method comprising the following steps:

- 5       - supply of an initial substrate comprising an Si or SiC support (1) bearing a layer (2) of SiO<sub>2</sub> whereon a thin layer (3) of SiC is transferred,

      - epitaxy of SiC (4) on the thin layer (3) of SiC.

The epitaxy is conducted at the following temperatures :

- 10       - from 1450°C to obtain 6H or 4H polytype epitaxy (4) on a transferred thin 6H or 4H polytype layer (3) respectively, if the support (1) consists of SiC,

- from 1350°C to obtain 3C polytype epitaxy (4) on a transferred thin 3C polytype layer (3), if the support (1)  
15 consists of Si or SiC,

- from 1350°C to obtain 6H or 4H polytype epitaxy (4) on a transferred thin 6H or 4H polytype layer (3) respectively, if the support (1) consists of Si.

Figure 1